Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!

Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832
Email & Skype: info@chipsmall.com Web: www.chipsmall.com
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China

ADVANCED POWER TECHNOLOGY RF®

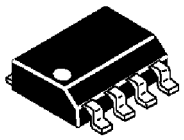
MRF8372, R1, R2
MRF8372G, R1, R2

RF & MICROWAVE DISCRETE LOW POWER TRANSISTORS

* G Denotes RoHS Compliant, Pb Free Terminal Finish

Features

- **Specified @ 12.5V, 870 MHz characteristics**
- **Output Power = 750 mW**
- **Minimum Gain = 8.0dB**
- **Efficiency 60% Typical**
- **Cost Effective SO-8 package**



SO-8

R1 suffix–Tape and Reel, 500 units
R2 suffix–Tape and Reel, 2500 units

DESCRIPTION: Designed primarily for wideband large signal stages in the 800 MHz and UHF frequency ranges.

ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V_{CEO}	Collector-Emitter Voltage	16	V
V_{CBO}	Collector-Base Voltage	30	V
V_{EBO}	Emitter-Base Voltage	3	V
I_C	Collector Current	200	mA
P_D	Total Device Dissipation @ TC = 50ºC	2.2	W
T_{STG}	Storage Junction Temperature Range	-65 to +150	ºC

Thermal Data

$R_{TH(J-C)}$	Thermal Resistance Junction-Case	45	°C/W

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions	Value			
		Min.	Typ.	Max.	Unit
BV_{CEO}	I_C = 5.0 mA, I_B = 0	16	-	-	V
BV_{CES}	Ic = 5.0 mA, V_{BE} = 0	30	-	-	V
BV_{EBO}	I_E = 0.1 mA, I_C = 0	3.0	-	-	V
I_{CES}	V_{CE} = 15 V, V_{BE} = 0 V	-	-	0.1	mA
HFE	V_{CE} = 5.0 v, Ic = 50 mA	30	-	200	-

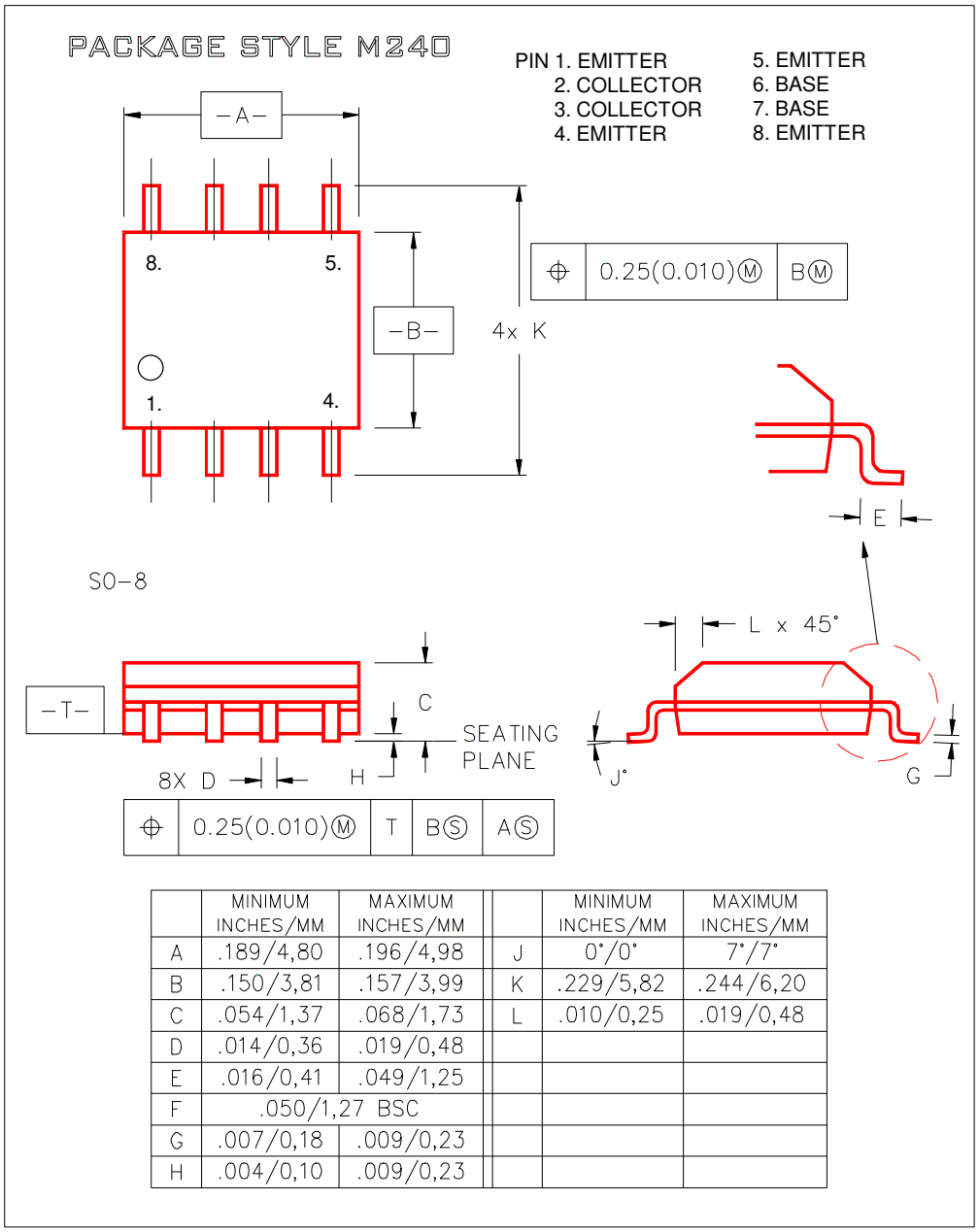
FUNCTIONAL

Symbol	Test Conditions	Value			
		Min.	Typ.	Max.	Unit
G_{PE}	f = 870 MHz, P_{OUT} = 0.75W, V_{CE} = 12.5V	8.0	9.5	-	dB
η_c	f = 870MHz, P_{OUT} = 0.75W, V_{CE} = 12.5V	50	60	-	%
C_{OB}	V_{CB} = 15 V, f = 1.0 MHz	-	-	2.75	pf

MRF8372, R1, R2

MRF8372G, R1, R2

PACKAGE MECHANICAL DATA



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM		MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.189/4,80	.196/4,98	J	0°/0°	7°/7°
B	.150/3,81	.157/3,99	K	.229/5,82	.244/6,20
C	.054/1,37	.068/1,73	L	.010/0,25	.019/0,48
D	.014/0,36	.019/0,48			
E	.016/0,41	.049/1,25			
F	.050/1,27 BSC				
G	.007/0,18	.009/0,23			
H	.004/0,10	.009/0,23			